

July 2013

FCPF380N60_F152

N-Channel SuperFET[®] II MOSFET 600 V, 10.2 A, 380 m Ω

Features

- 650 V @T_{.1} = 150°C
- Max. R_{DS(on)} = 380 mΩ
- Ultra low gate charge (typ. $Q_g = 30 \text{ nC}$)
- Low effective output capacitance (typ. C_{oss}.eff = 95 pF)
- 100% avalanche tested

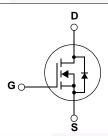
Aplications

- LCD / LED / PDP TV Lighting
- · Solar Inverter
- AC-DC Power Supply

Description

SuperFET[®]II MOSFET is Fairchild Semiconductor significant from this property of the super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is suitable for various AC/DC power conversion for system miniaturization and higher efficiency.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

| Symbol | | Parameter | | FCPF380N60_F152 | Unit | |
|---|--|--------------------------------------|-------------------|-----------------|------|--|
| V _{DSS} | Drain to Source Voltage | | | 600 | V | |
| V | Gate to Source Voltage | -DC | | ±20 | V | |
| V _{GSS} Gate to Source Voltage | -AC | (f>1HZ) | ±30 | V | | |
| | Drain Current | -Continuous (T _C = 25°C) | | 10.2* | ^ | |
| ID | Drain Current | -Continuous (T _C = 100°C) | | 6.4* | A | |
| I _{DM} | Drain Current | - Pulsed | - Pulsed (Note 1) | | Α | |
| E _{AS} | Single Pulsed Avalanche En | ergy | (Note 2) | 211.6 | mJ | |
| I _{AR} | Avalanche Current (Note 1) | | (Note 1) | 2.3 | Α | |
| E _{AR} | Repetitive Avalanche Energy (Note 1) | | (Note 1) | 1.06 | mJ | |
| dv/dt | Peak Diode Recovery dv/dt | | (Note 3) | 20 | 1// | |
| αν/αι | MOSFET dv/dt | | | 100 | V/ns | |
| ר | Dower Dissinction | (T _C = 25°C) | | 31 | W | |
| P_{D} | Power Dissipation | - Derate above 25°C | | 0.25 | W/°C | |
| T _J , T _{STG} | Operating and Storage Temp | perature Range | | -55 to +150 | °C | |
| T _L | Maximum Lead Temperature 1/8" from Case for 5 Second | • • | | 300 | °C | |

^{*}Drain current limited by maximum junction temperature

Thermal Characteristics

| Symbol | Parameter | FCPF380N60_F152 | Unit |
|-----------------|---|-----------------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 4 | |
| $R_{\theta CS}$ | Thermal Resistance, Case to Heat Sink (Typical) | 0.5 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 62.5 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Eco Status | Packaging Type | Quantity |
|----------------|-----------------|---------|------------|----------------|----------|
| FCPF380N60 | FCPF380N60_F152 | TO-220F | Green 🏈 | Tube | 50 |

For Fairchild's definition of "green" Eco Status, please visit: http://www.fairchildsemi.com/company/green/rohs_green.html.

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|---|---|---|------|------|------|------|
| Off Charac | cteristics | | | | | |
| D\/ | Drain to Source Breakdown Voltage | $V_{GS} = 0V, I_D = 10mA, T_J = 25^{\circ}C$ | 600 | - | - | V |
| BV _{DSS} Drain to S | Drain to Source Breakdown voltage | $V_{GS} = 0V, I_D = 10mA, T_J = 150^{\circ}C$ | 650 | - | - | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_{,I}}$ | Breakdown Voltage Temperature Coefficient | I _D = 10mA, Referenced to 25°C | - | 0.6 | - | V/°C |
| BV _{DS} | Drain-Source Avalanche Breakdown Voltage | V _{GS} = 0V, I _D = 10A | - | 700 | - | V |
| | Zero Gate Voltage Drain Current | $V_{DS} = 480V, V_{GS} = 0V$ | - | - | 10 | |
| IDSS | Zero Gate voltage Drain Current | $V_{DS} = 480V, T_{C} = 125^{\circ}C$ | - | - | 10 | μА |
| I _{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 20V, V_{DS} = 0V$ | - | - | ±100 | nA |

On Characteristics

| V _{GS(th)} | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_{D} = 250 \mu A$ | 2.5 | - | 3.5 | V |
|---------------------|--------------------------------------|--------------------------------------|-----|------|------|---|
| R _{DS(on)} | Static Drain to Source On Resistance | $V_{GS} = 10V, I_D = 5A$ | - | 0.33 | 0.38 | Ω |
| 9 _{FS} | Forward Transconductance | $V_{DS} = 20V, I_{D} = 5A$ | - | 11 | - | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V 05V V 0V | - \ | 1250 | 1665 | pF |
|-----------------------|-------------------------------|---|-----|------|------|----|
| C _{oss} | Output Capacitance | $V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz | | 905 | 1205 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 45 | 60 | pF |
| C _{oss} | Output Capacitance | $V_{DS} = 380V, V_{GS} = 0V, f = 1MHz$ | - | 23 | - | pF |
| C _{oss} eff. | Effective Output Capacitance | $V_{DS} = 0V$ to 480V, $V_{GS} = 0V$ | - | 95 | - | pF |
| Q _{g(tot)} | Total Gate Charge at 10V | $V_{DS} = 380V, I_{D} = 5A$ | - | 30 | 40 | nC |
| Q_{gs} | Gate to Source Gate Charge | V _{GS} = 10V | - | 5 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | (Note 4) | - | 10 | - | nC |
| ESR | Equivalent Series Resistance | f = 1MHz | - / | 1 | - | Ω |

Switching Characteristics

| t _{d(on)} | Turn-On Delay Time | | _ | 14 | 38 | ns |
|---------------------|---------------------|-------------------------------|---|----|-----|----|
| t _r | | $V_{DD} = 380V, I_{D} = 5A$ | - | 7 | 24 | ns |
| t _{d(off)} | Turn-Off Delay Time | $V_{GS} = 10V, R = 4.7\Omega$ | - | 45 | 100 | ns |
| t _f | Turn-Off Fall Time | (Note 4) | - | 6 | 22 | ns |

Drain-Source Diode Characteristics

| Is | Maximum Continuous Drain to Source Dioc | Maximum Continuous Drain to Source Diode Forward Current | | | 10.2 | Α |
|-----------------|--|--|---|-----|------|----|
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | | _ | 30.6 | Α |
| V_{SD} | Drain to Source Diode Forward Voltage V _{GS} = 0V, I _{SD} = 5A | | - | - | 1.2 | V |
| t _{rr} | Reverse Recovery Time | $V_{GS} = 0V$, $I_{SD} = 5A$ | - | 240 | \\ - | ns |
| Q _{rr} | Reverse Recovery Charge $dI_F/dt = 100A/\mu s$ | | - | 2.7 | - | μС |

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. I_{AS} = 2.3A, V_{DD} = 50V, R_{G} = 25 $\!\Omega$, Starting T_{J} = 25 $^{\circ}C$
- 3. I_{SD} $\leq 5.1 \text{A}, \text{ di/dt} \leq 200 \text{A/}\mu\text{s}, \text{ V}_{DD} \leq \text{BV}_{DSS}, \text{ Starting T}_J = 25^{\circ}\text{C}$
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

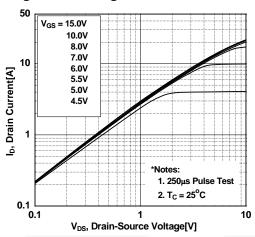


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

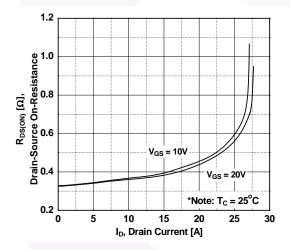


Figure 5. Capacitance Characteristics

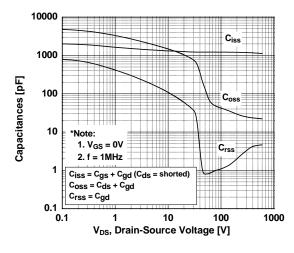


Figure 2. Transfer Characteristics

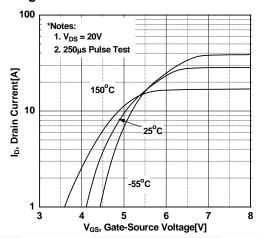


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

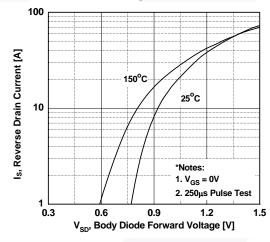
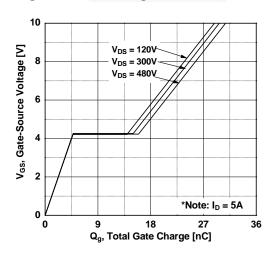


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

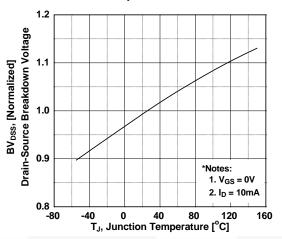


Figure 9. Maximum Safe Operating Area vs. Case Temperature

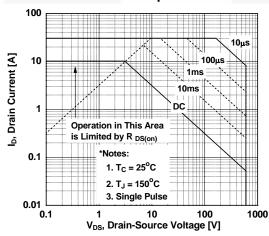


Figure 11. Maximum Drain Current

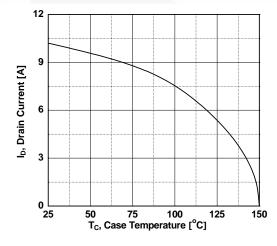


Figure 8. On-Resistance Variation vs. Temperature

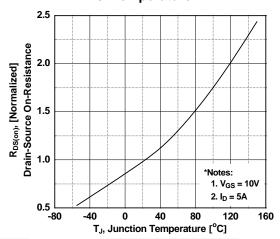
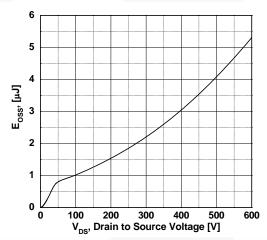
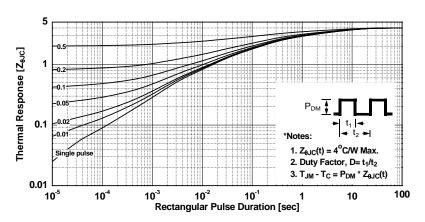


Figure 10. Eoss vs. Drain to Source Voltage Switching Capability

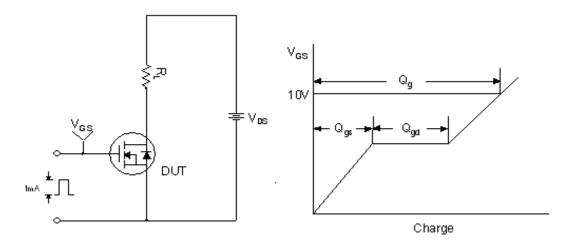


Typical Performance Characteristics (Continued)

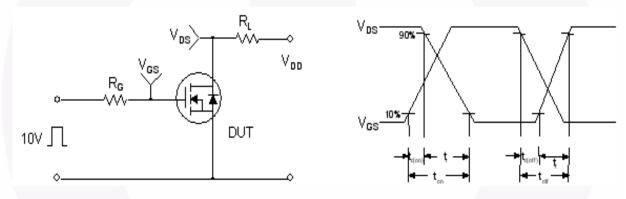
Figure 12. Transient Thermal Response Curve



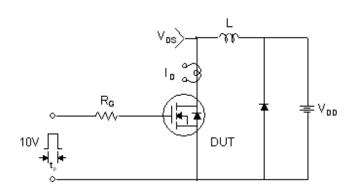
Gate Charge Test Circuit & Waveform

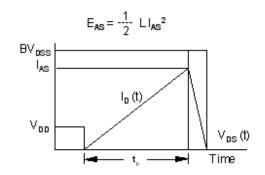


Resistive Switching Test Circuit & Waveforms

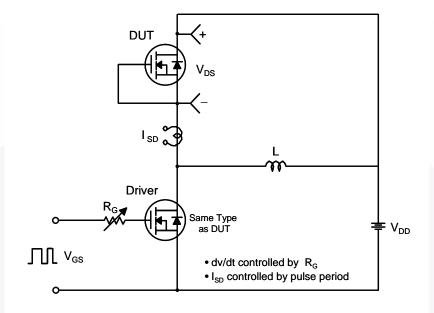


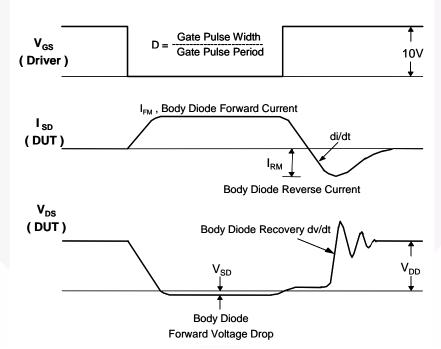
Unclamped Inductive Switching Test Circuit & Waveforms





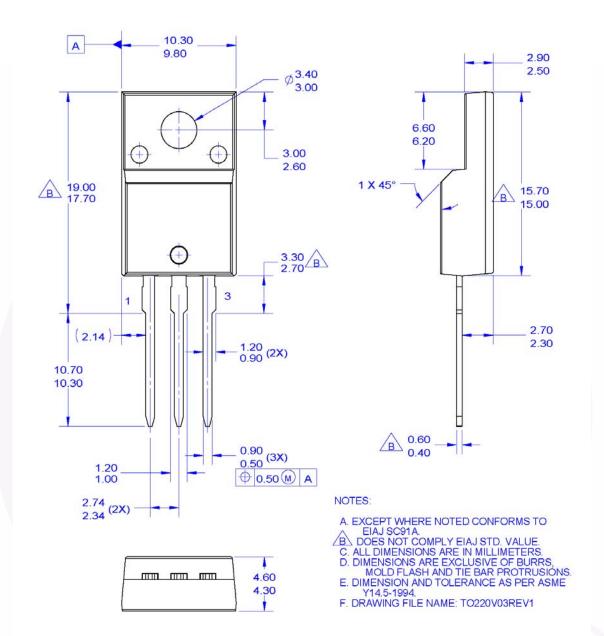
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-220F



* Front/Back Side Isolation Voltage : AC 2500V

TO-220, MOLDED, 3LD, FULL PACK, EIAJ SC91

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